

Displacement damage stabilization by hydrogen presence under simultaneous W ion damaging and D ion exposure

S. Markelj¹, T. Schwarz-Selinger², M. Pečovnik¹, M. Kelemen^{1,3}

¹Jožef Stefan Institute, Ljubljana, Slovenia

²Max-Planck-Institut für Plasmaphysik (IPP), Garching, Germany

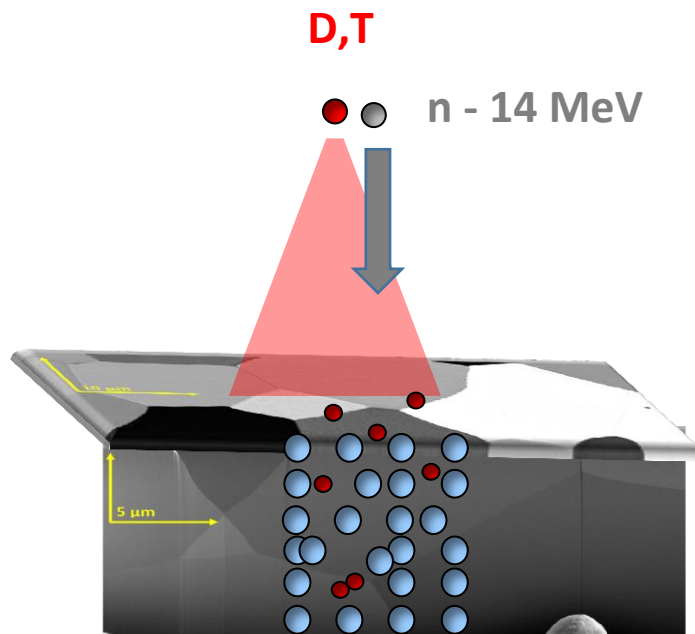
³Jožef Stefan International Postgraduate School, Jamova cesta 39, 1000 Ljubljana, Slovenia

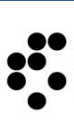


Tungsten –plasma facing material

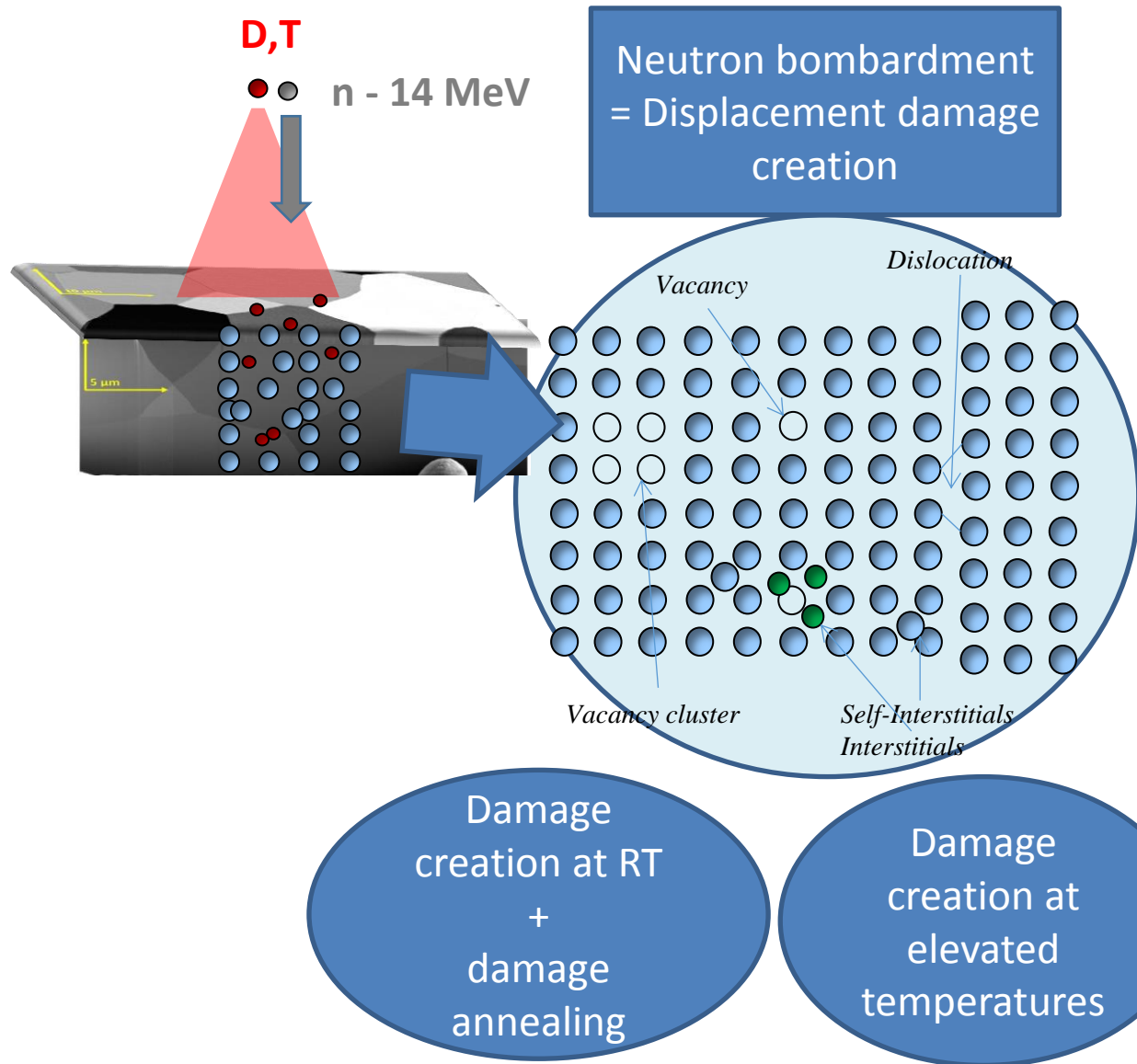
Fusion device scenario

D/T plasma exposure + neutron irradiation





Tungsten –plasma facing material





Tungsten –plasma facing material

Fuel implantation

- ions and neutrals - energy few eV – keV;
- High fluxes up to $10^{24} \text{ m}^{-2} \text{ s}^{-1}$

Implantation

Reflection

Adsorption

Recombination

Desorption

Trapping

Diffusion

Hydrogen

Metal atom

D,T

n - 14 MeV

Neutron bombardment
= Displacement damage
creation

Vacancy

Dislocation

Vacancy cluster

Self-Interstitials
Interstitials

Damage
creation at RT
+
damage
annealing

Damage
creation at
elevated
temperatures

Fuel transport:
diffusion
trapping
de-trapping

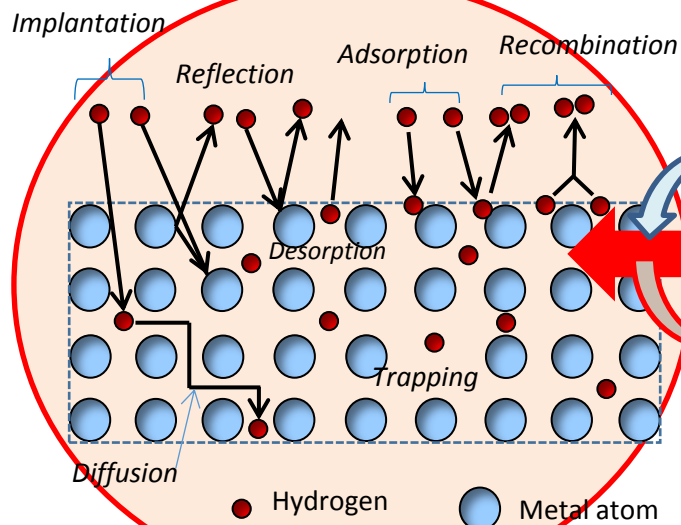
Fuel
retention



Tungsten –plasma facing material

Fuel implantation

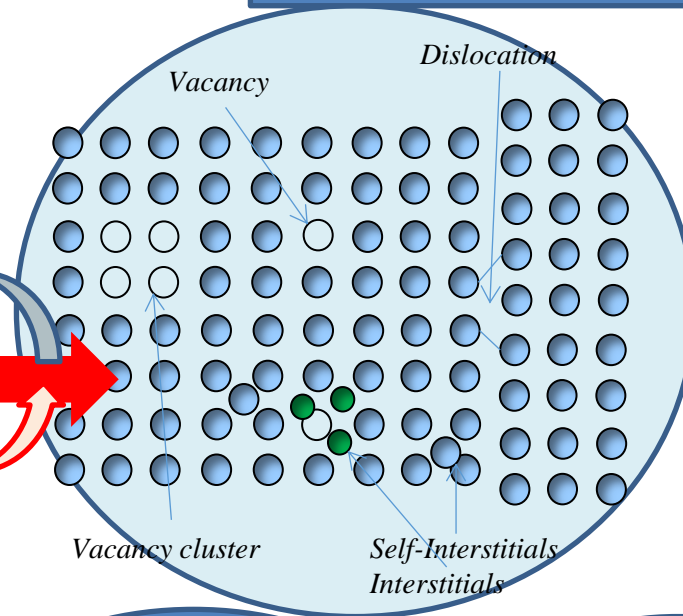
- ions and neutrals - energy few eV – keV;
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Fuel transport:
diffusion
trapping
de-trapping

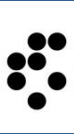
Fuel
retention

Neutron bombardment
= Displacement damage
creation

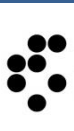


Damage
creation at RT
+
damage
annealing

Damage
creation at
elevated
temperatures

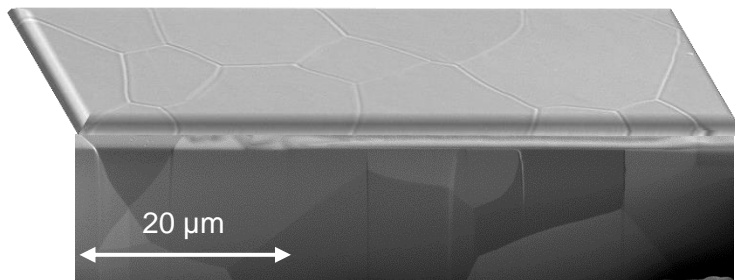


- *Different displacement damaging procedures*
- *Comparison between:*
 - *Sequential W ion irradiation and D exposure*
 - *Simultaneous W ion irradiation and D exposure*
- *Comparison atoms versus ions*
- *Conclusions*

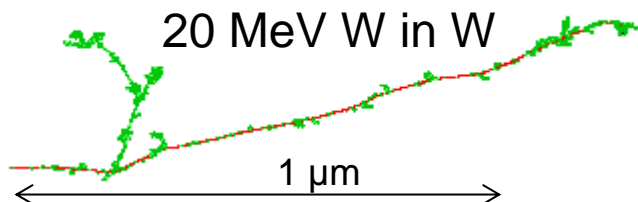


14 MeV neutron irradiation

Displacement damage creation



W self-damaging



SRIM calculation of ion trajectory

Influence of neutron irradiation on D retention
activation of samples, long irradiation time,
14 MeV neutrons not available (fission neutrons)!

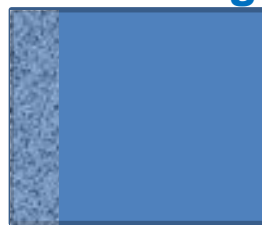


High energy ion damaging

MeV W ion irradiation = Surrogate for neutron irradiation

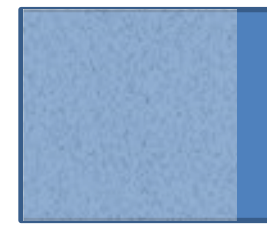
- Dense cascades and no chemical effect
- No transmutation

Ion damaging



→
Few μm

neutron damaging



→
Few cm



Displacement damage creation MeV W ion irradiation

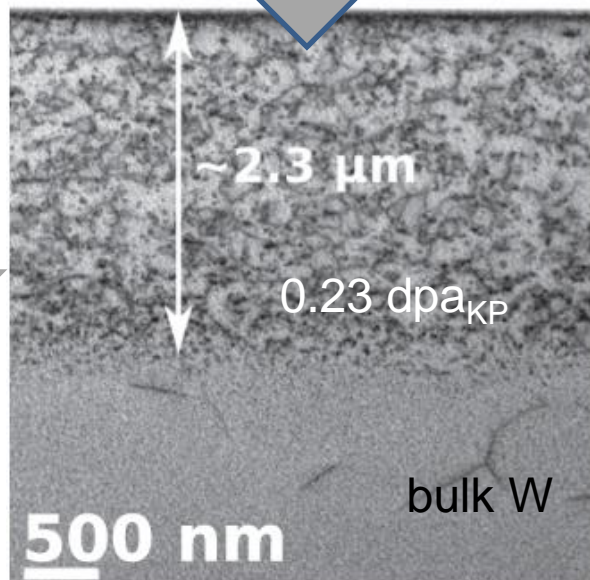


W self-damaging

W ions 20 MeV

7.9×10^{17} W/m²

W⁶⁺ 20 MeV



Recrystallized W

W ion irradiation by MeV W ions

- Creation of displacement damage

**Damaged layer characterization by
Scanning Transmission**

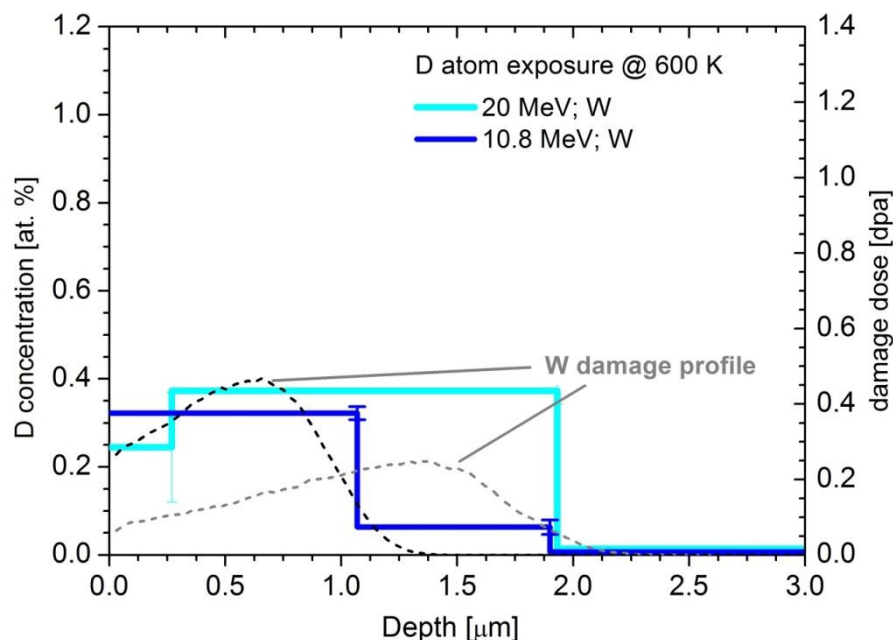
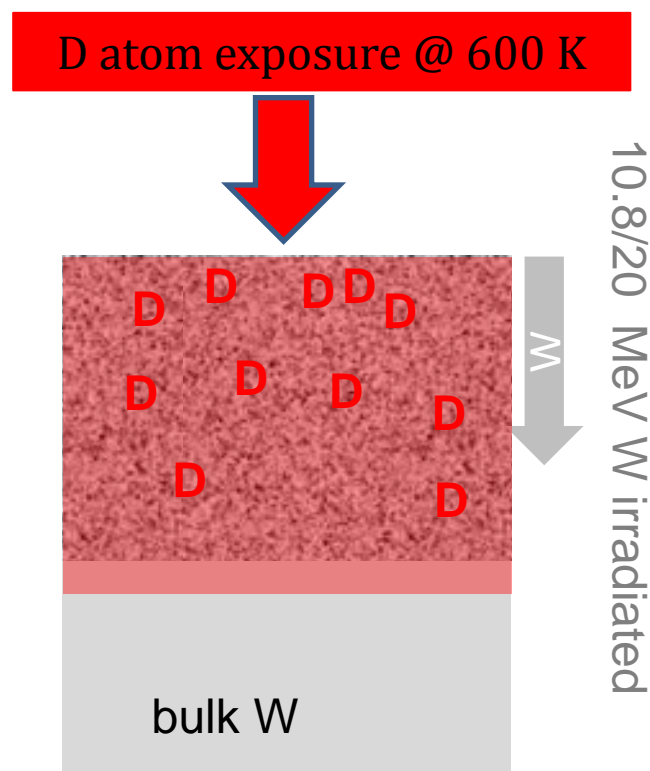
Electron Microscopy [Zaloznik et al.
Phys Scr. T167 (2016) 014031]



Displacement damage creation MeV W ion irradiation

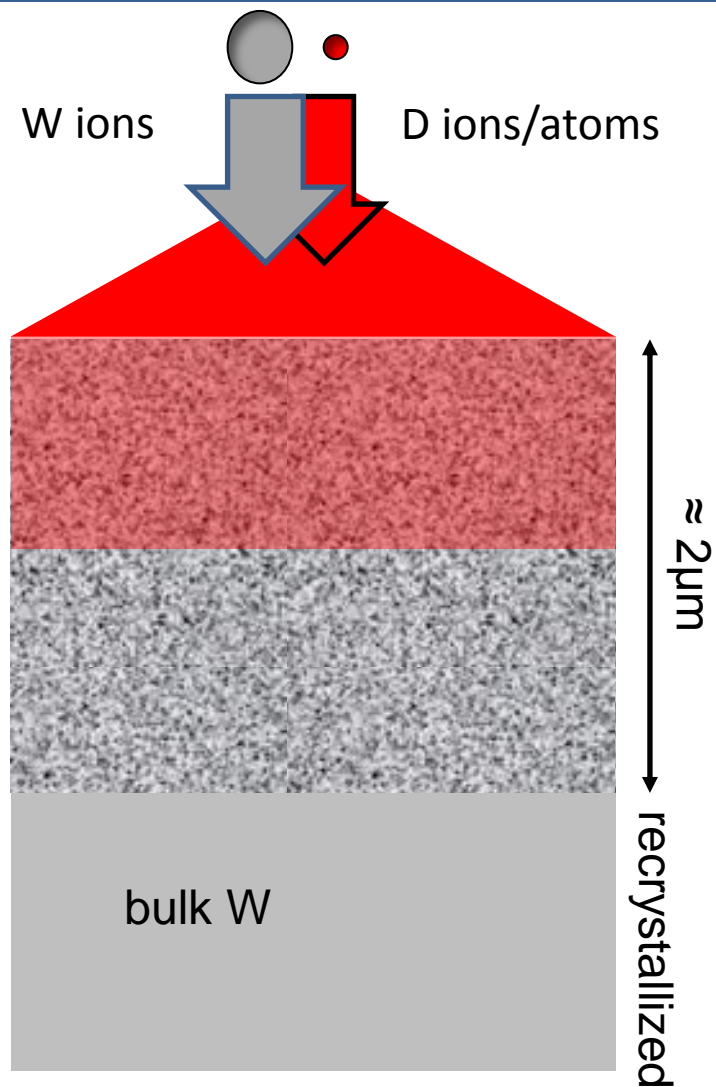
W ion irradiation by MeV W ions

- Creation of displacement damage
- Increased fuel retention in ion damaged W material from $\sim 10^{-3}$ at. % \nearrow ~ 1 at. %
- D saturation observed at damage dose > 0.2 dpa for RT W irradiation! [Alimov et al. JNM 2013, Hoen et al. NF 2012, Schwarz-Selinger FEC 2018]





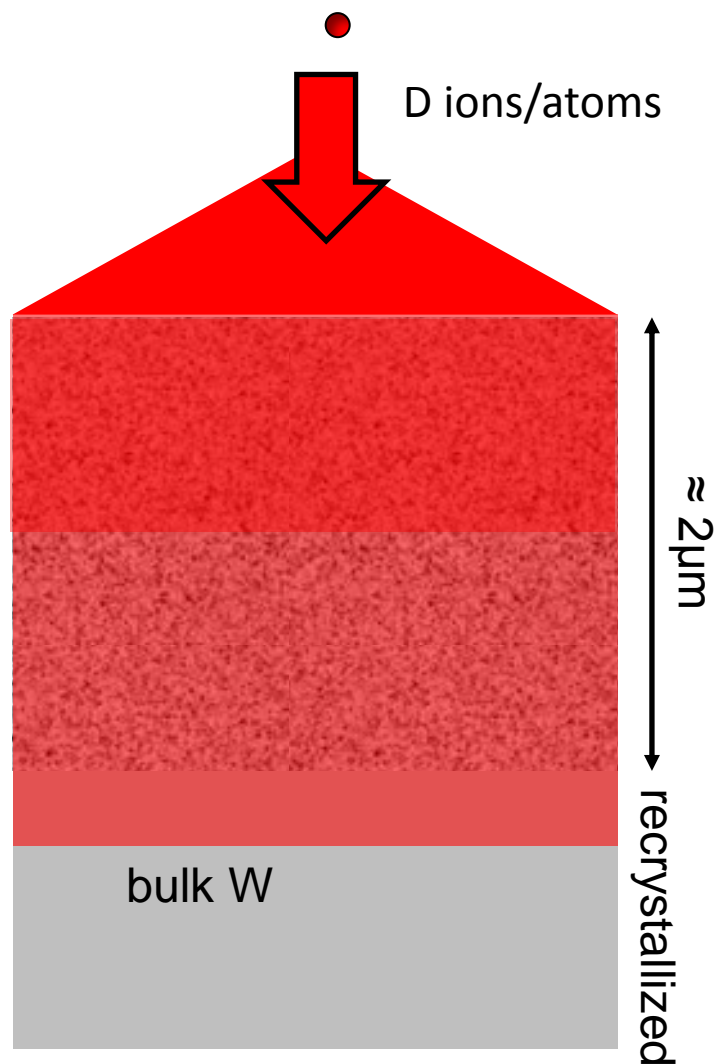
Simultaneous W/D exposure



Simultaneous W/D exposure:
W ion irradiation @ different high
D exposure temperatures



Simultaneous W/D-D exposure



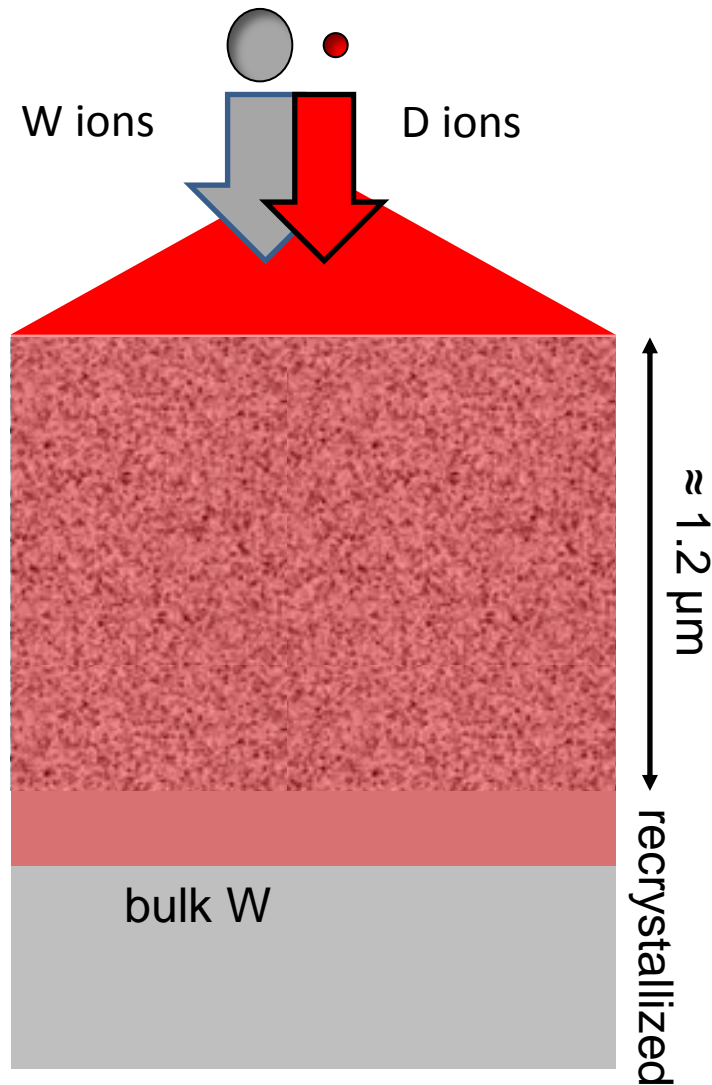
Simultaneous W/D-D exposure:
W ion irradiation @ different high temperatures
D exposure

-
D exposure @ low temperature to populate created traps

✓ D retention a way to determine defect concentration



Sequential W-D exposure



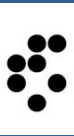
Sequential W-D exposure:

W ion irradiation @ different high temperatures

D exposure

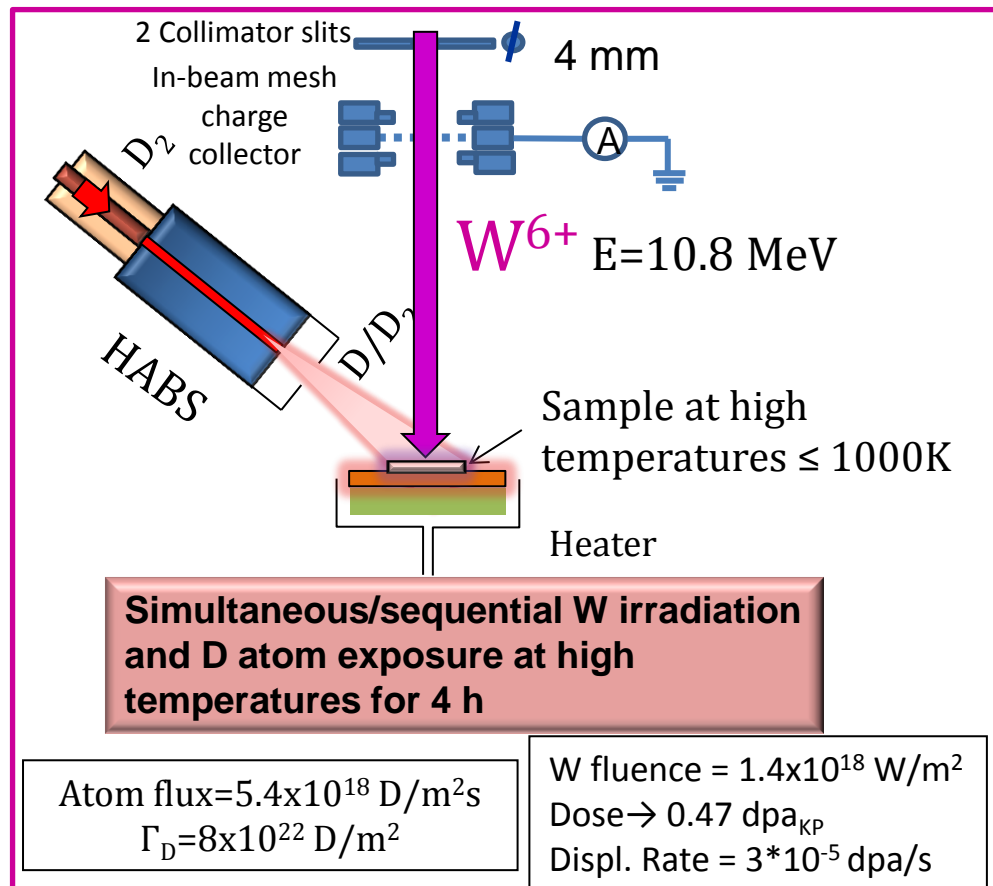
@ low temperature to populate created traps

✓ D retention a way to determine defect concentration



Experiment with atoms – 0.28 eV/D

- Simultaneous/sequential W/D, W-D atom loading
- Defect population - exposure D atoms @ 600 K – fluence 3.7×10^{23} D/m²



Analysis methods:

- Deuterium depth profile measurement by Nuclear Reaction Analysis (NRA)
- TDS – final step – D desorption kinetics and D amount

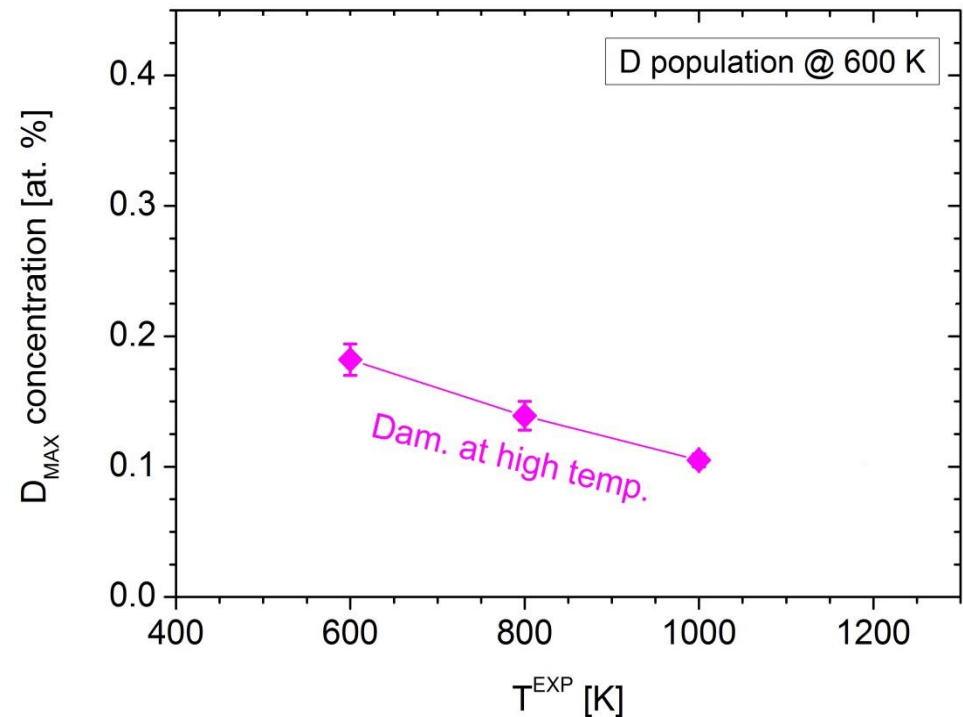
Effect of D presence – atom exposure

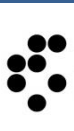
Comparison of D concentration

- Neutron damaging simulated by self implantation
- Simultaneous W ion damaging and D atom loading

Comparison to different damaging procedures

❖ *Sequential: Damage at T^{EXP} ; D population at 600 K*





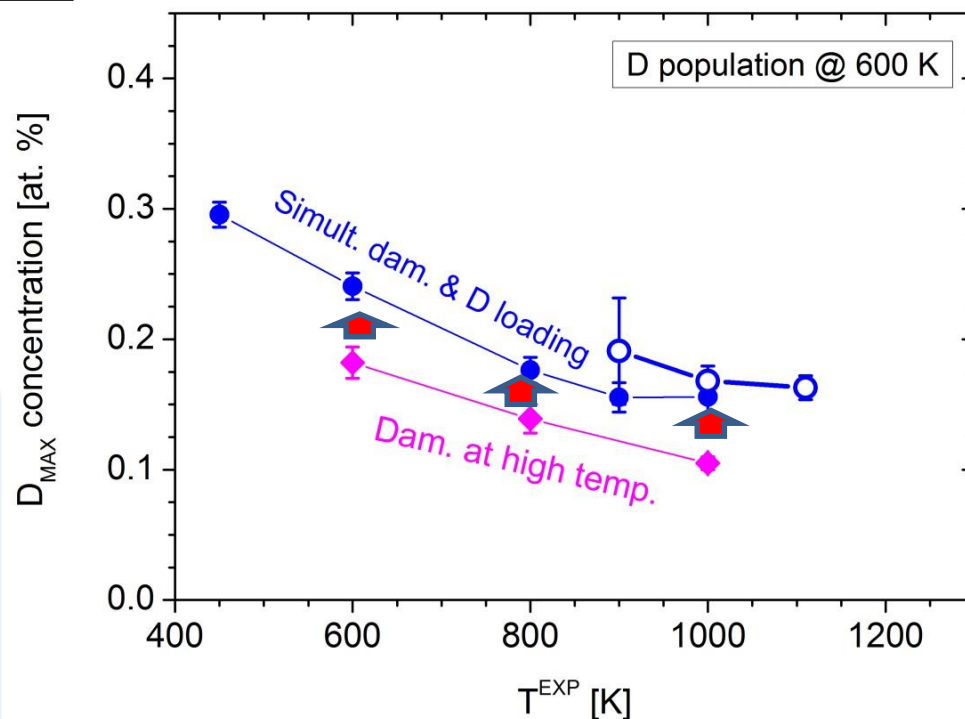
Effect of D presence – atom exposure Comparison of D concentration

- Neutron damaging simulated by self implantation
- Simultaneous W ion damaging and D atom loading

Comparison to different damaging procedures

- ❖ *Sequential: Damage at T^{EXP} ; D population at 600 K*
- ❖ *Simultaneous: Damage & D exposure at T^{EXP} ; D population at 600 K*

- ✓ **Observed synergistic effects but not dramatic – 30 % increase**
- ✓ **Competition between defect annihilation at elevated temp. and defect stabilization by D**



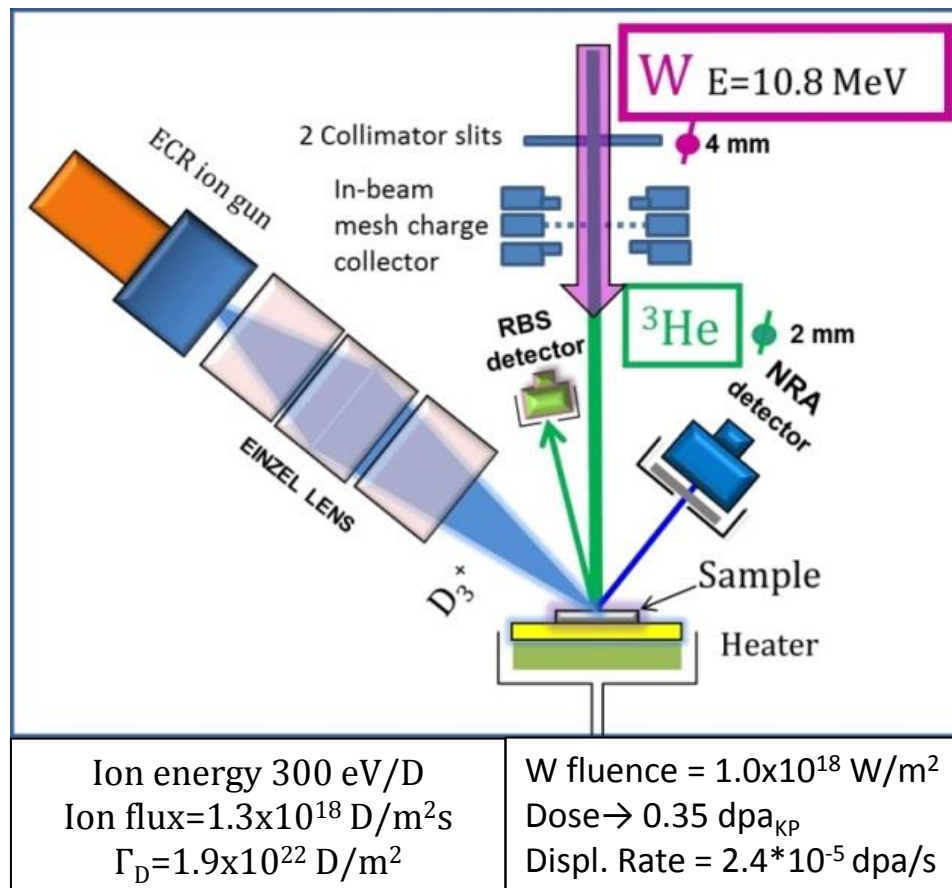
For more details see:

- S. Markelj, et al, Nuclear Materials and Energy 12 (2017) 169.
- E. Hodille et al. Nucl. Fusion **59** (2019) 016011



Experiment with ions– 300 eV/D

- Simultaneous/sequential W/D, W-D ion loading
- Defect population - exposure D ions @ 450 K – fluence 2.7×10^{23} D/m²



Analysis methods:

- Deuterium depth profile measurement by Nuclear Reaction Analysis (NRA)
- TDS – final step – D desorption kinetics and D amount

- S. Markelj et al, Nucl. Fusion (2019) in press
- M. Pecovnik et al. submitted to Nucl. Fusion



TDS - Sequential experiment

W ion damaging at 300 K – sequential D atom exposure at 600K

- ✓ Single peak
- ✓ Two de-trapping energies 1.82 eV and 2.06 eV

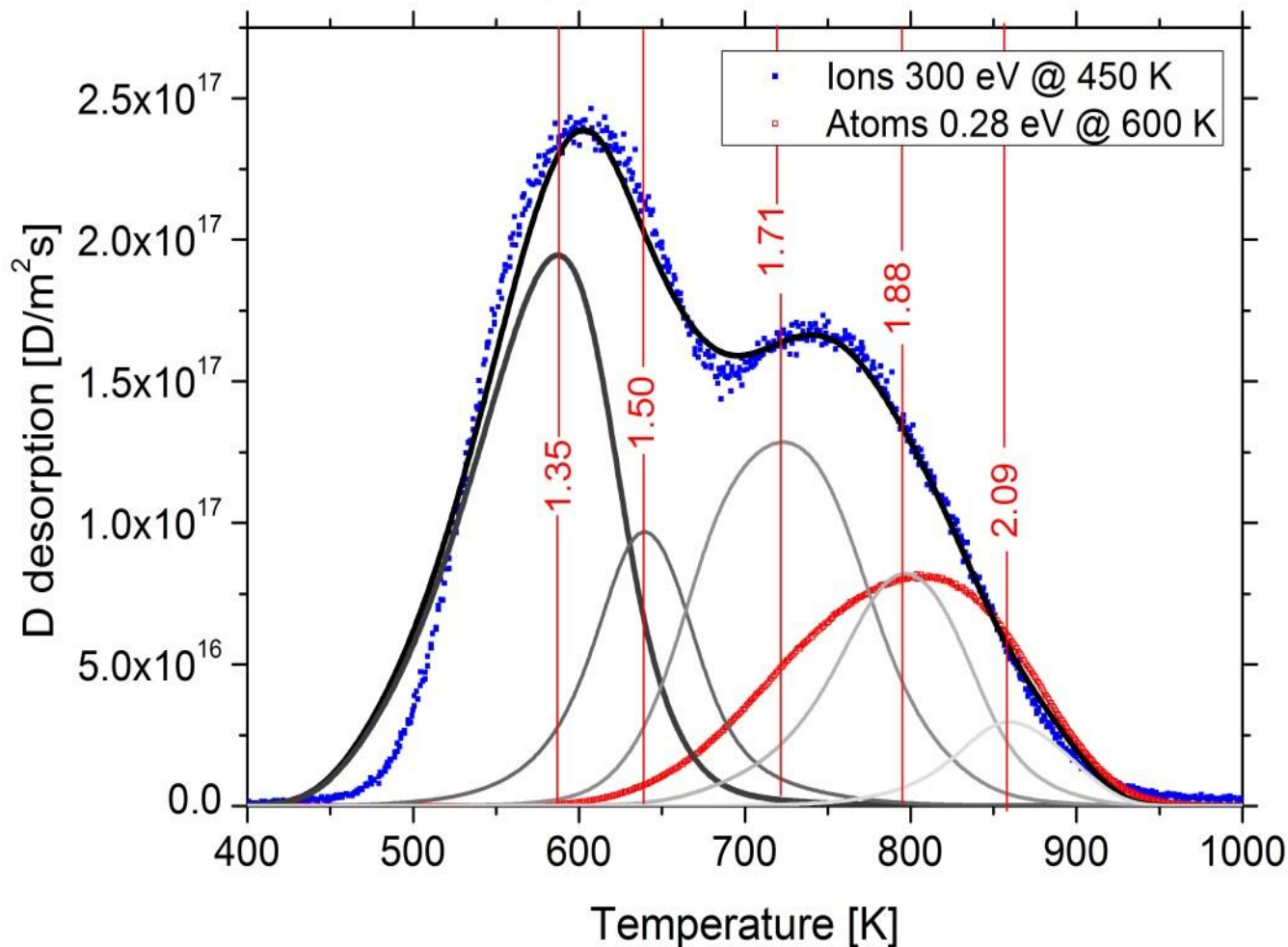
D ion exposure at 450K

- ✓ Double peak
- ✓ Five de-trapping energies 1.35 eV - 2.09 eV

- ✓ 3x higher D amount

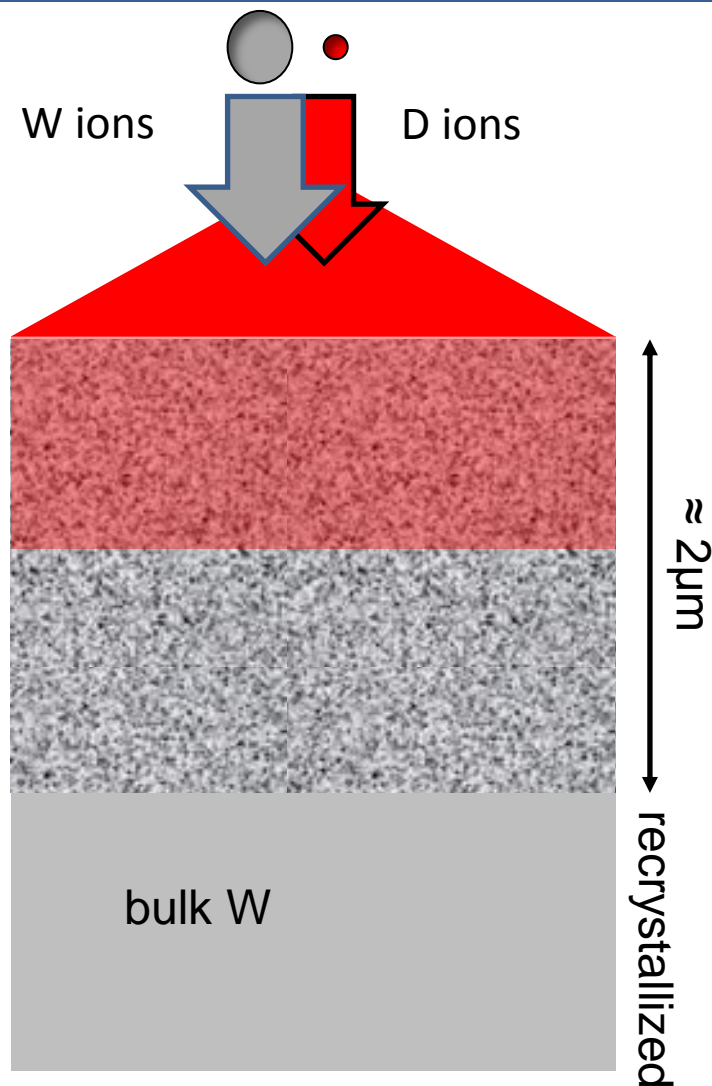
Rate equation modelling
(MHIMS, Hodille et al. JNM 2017)

Sequential W-D; W damaging @ 300 K





Simultaneous W/D exposure



Simultaneous W/D exposure:

W ion irradiation @ 450 K

D ion exposure

4h simultaneous W/D

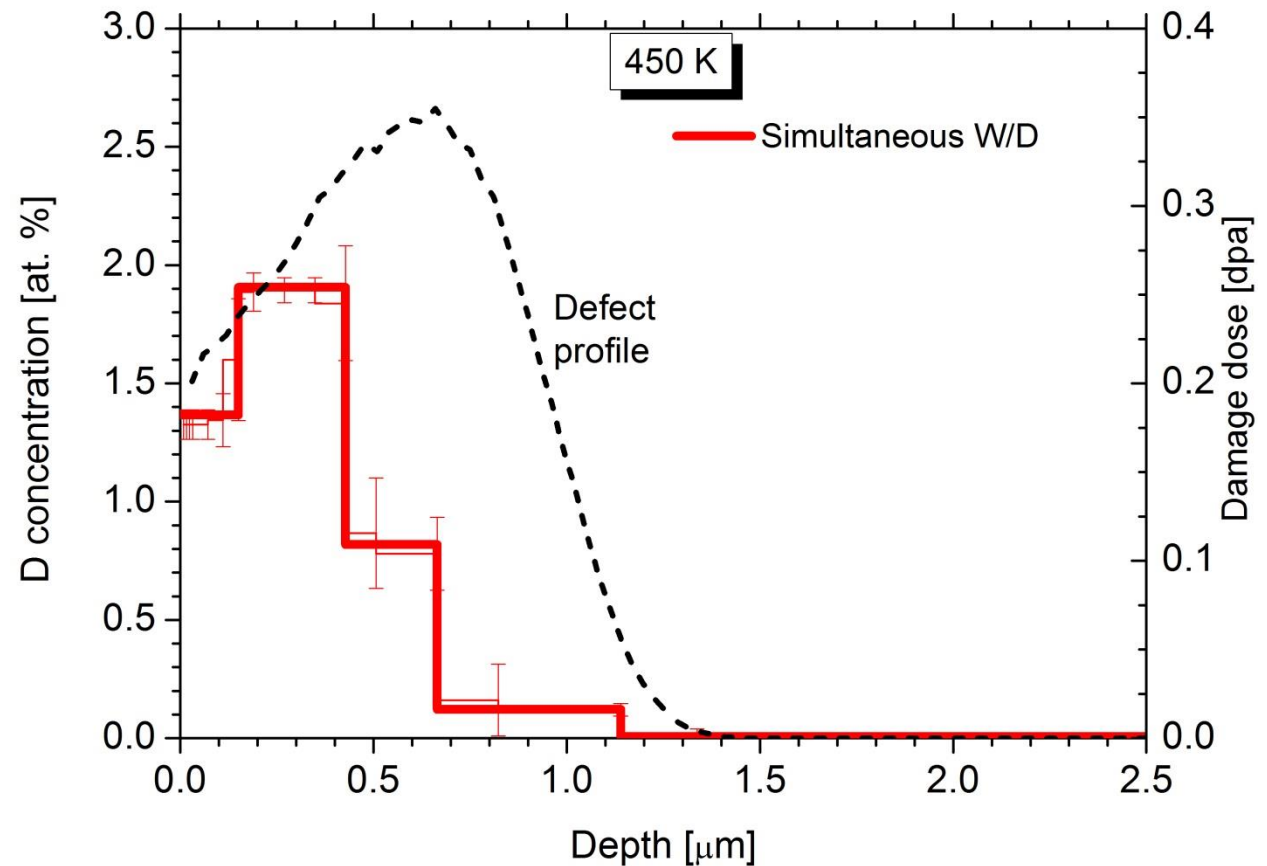
W ions – flux 9.73×10^{13} W/m²s – 0.34 dpa

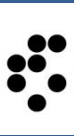
D ions - ion flux = 1.4×10^{18} D/m²s

$\Gamma_D = 2.0 \times 10^{22}$ D/m²

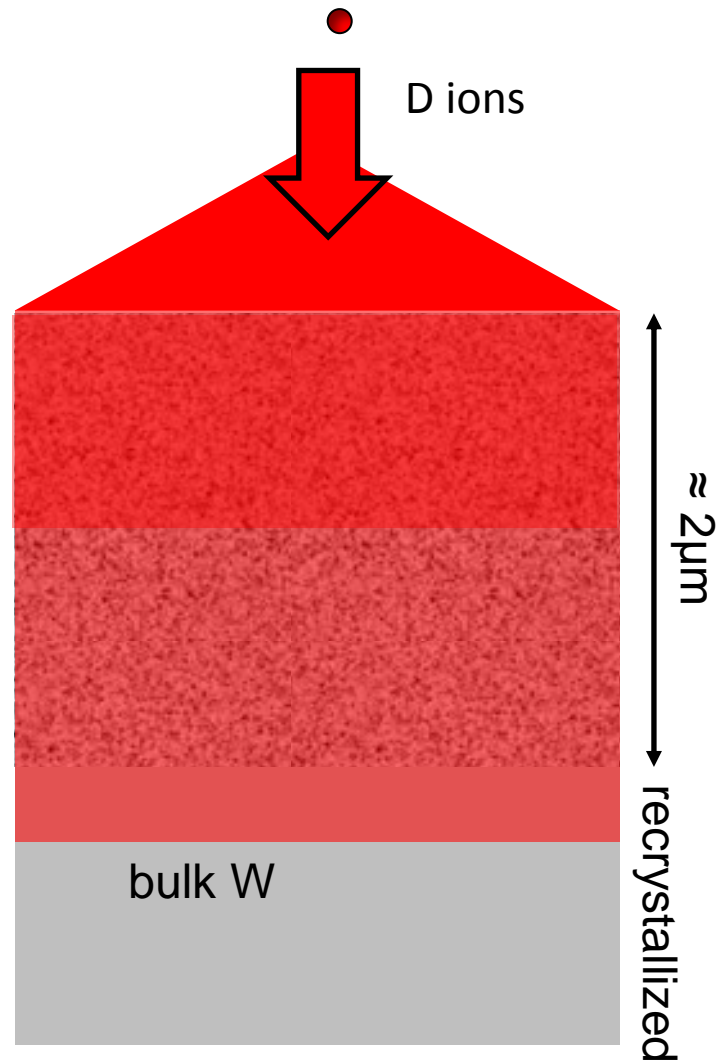
Simultaneous W/D exposure @ 450 K

D depth profile





Simultaneous W/D-D exposure @ 450 K



Simultaneous W/D-D exposure:

W ion irradiation @ 450 K

D ion exposure

+

D ion exposure

@ 450 K – to
populate created
traps

4h simultaneous W/D

W ions – flux 9.73×10^{13} W/m²s – 0.34 dpa

D ions - Ion flux = 1.4×10^{18} D/m²s.

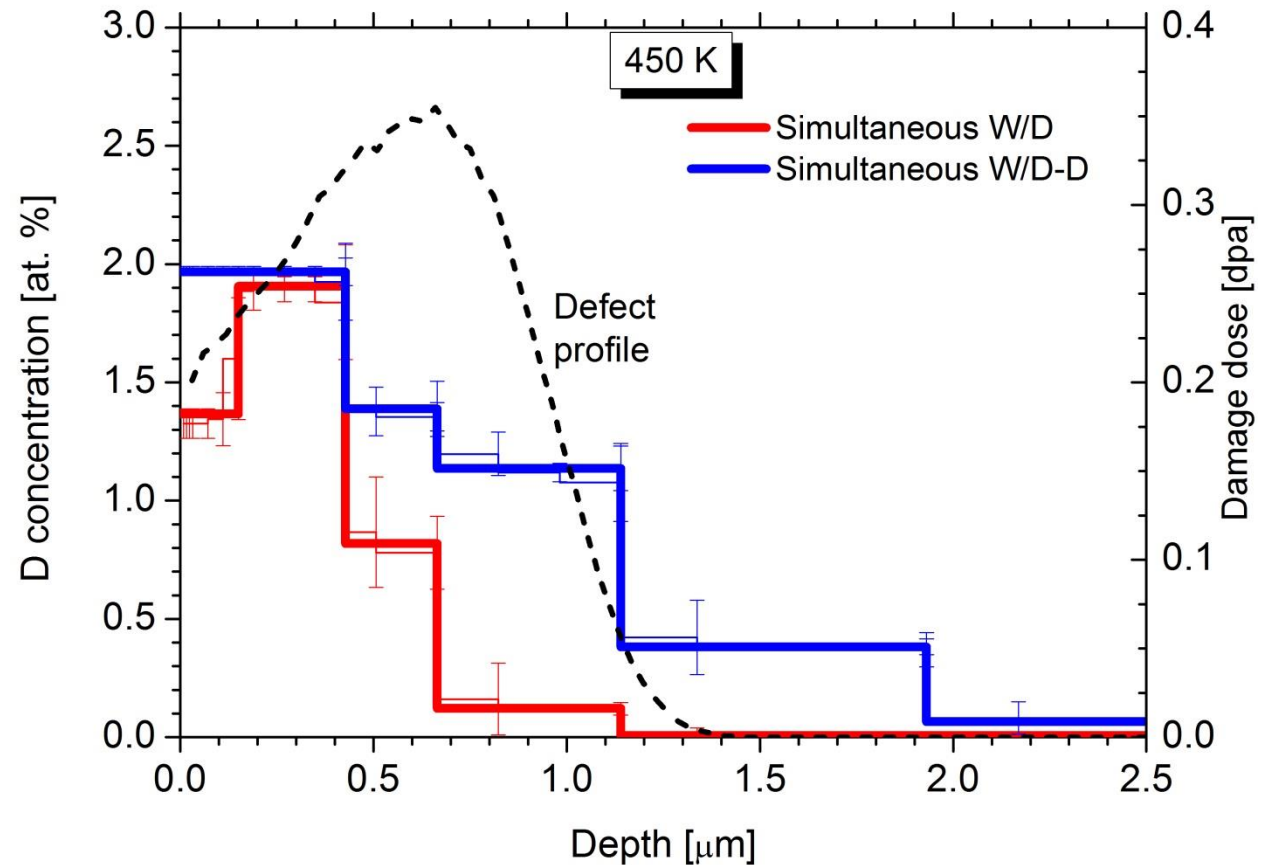
D fluence = 2.0×10^{22} D/m²

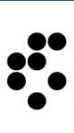
+

41h D ion exposure - D fluence 2.1×10^{23} D/m²

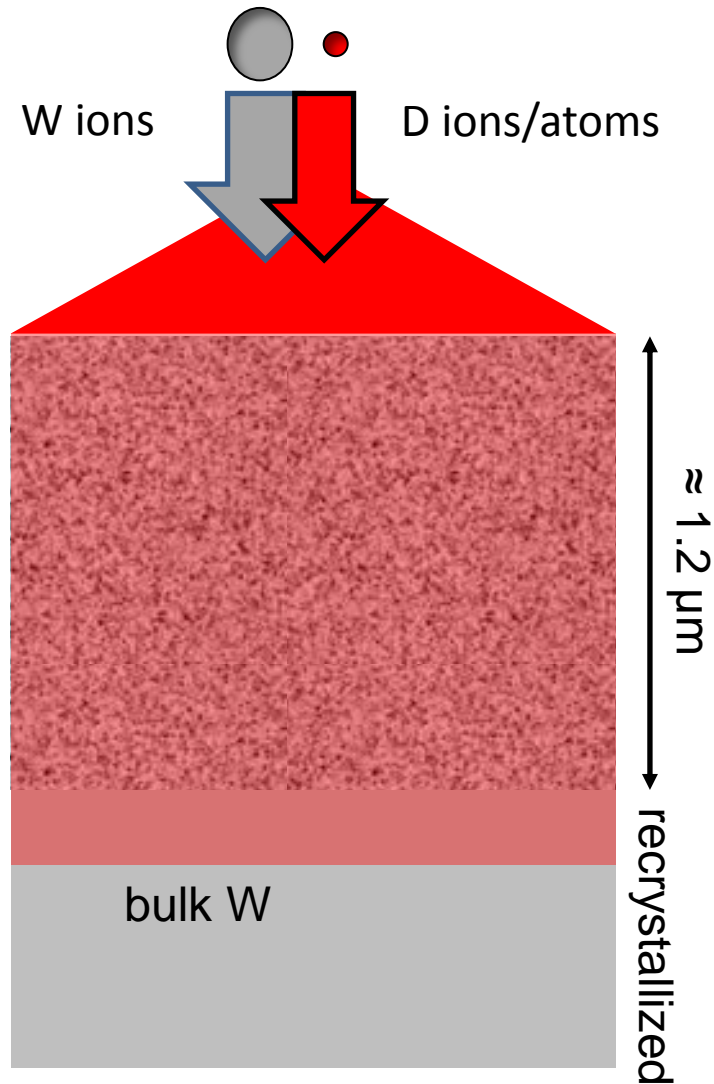
Simultaneous W/D-D exposure @ 450 K

D depth profile





Sequential W-D exposure



Sequential W-D exposure:

W ion irradiation @ 450 K

+

D ion exposure

@ 450 K to populate
created traps

4h W irradiation

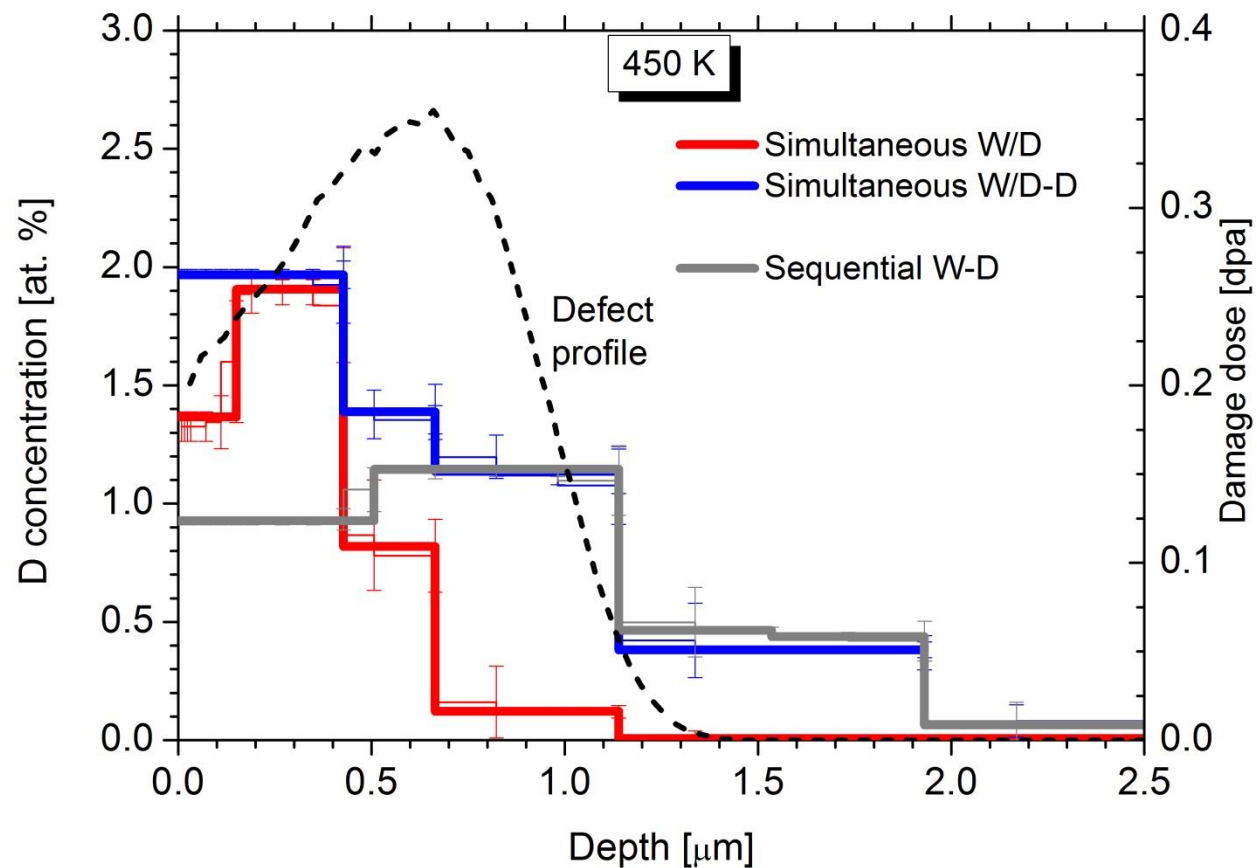
W ions – flux 9.73×10^{13} W/m²s – 0.34 dpa

+

39 h D ion exposure - D fluence 2.0×10^{23} D/m²



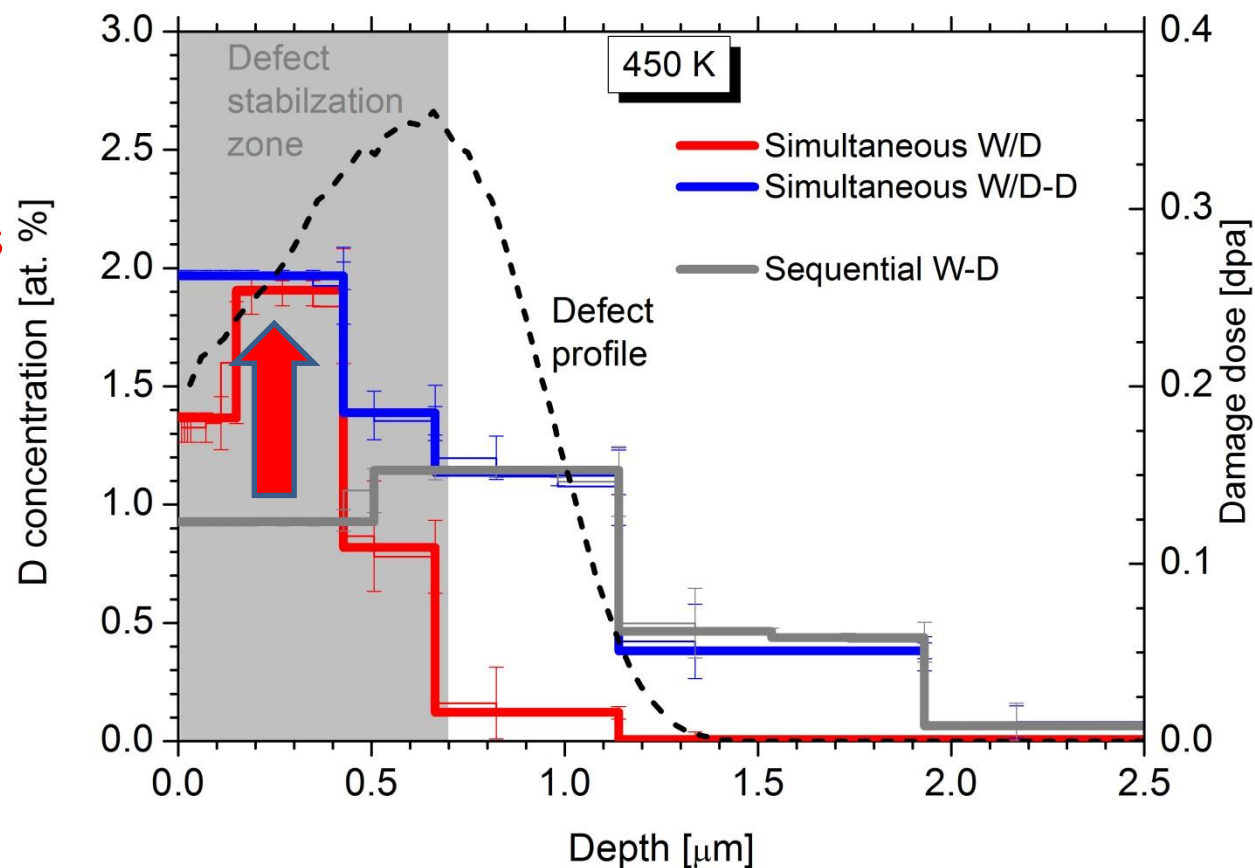
D depth profile comparison @ 450 K





D depth profile comparison @ 450 K

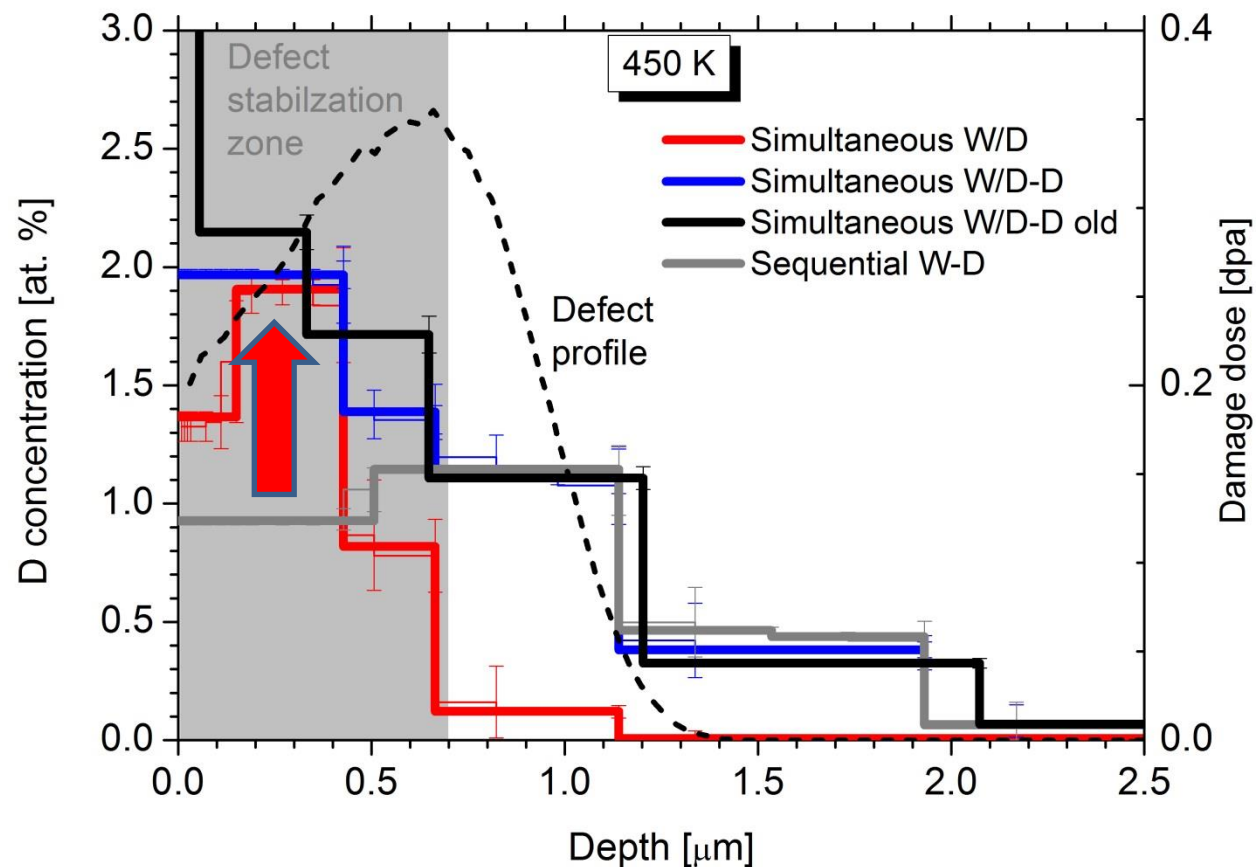
- Difference in D concentration in the region where D was trapped during the 1. step – simultaneous W/D
- Factor of 2 difference





D depth profile comparison @ 450 K

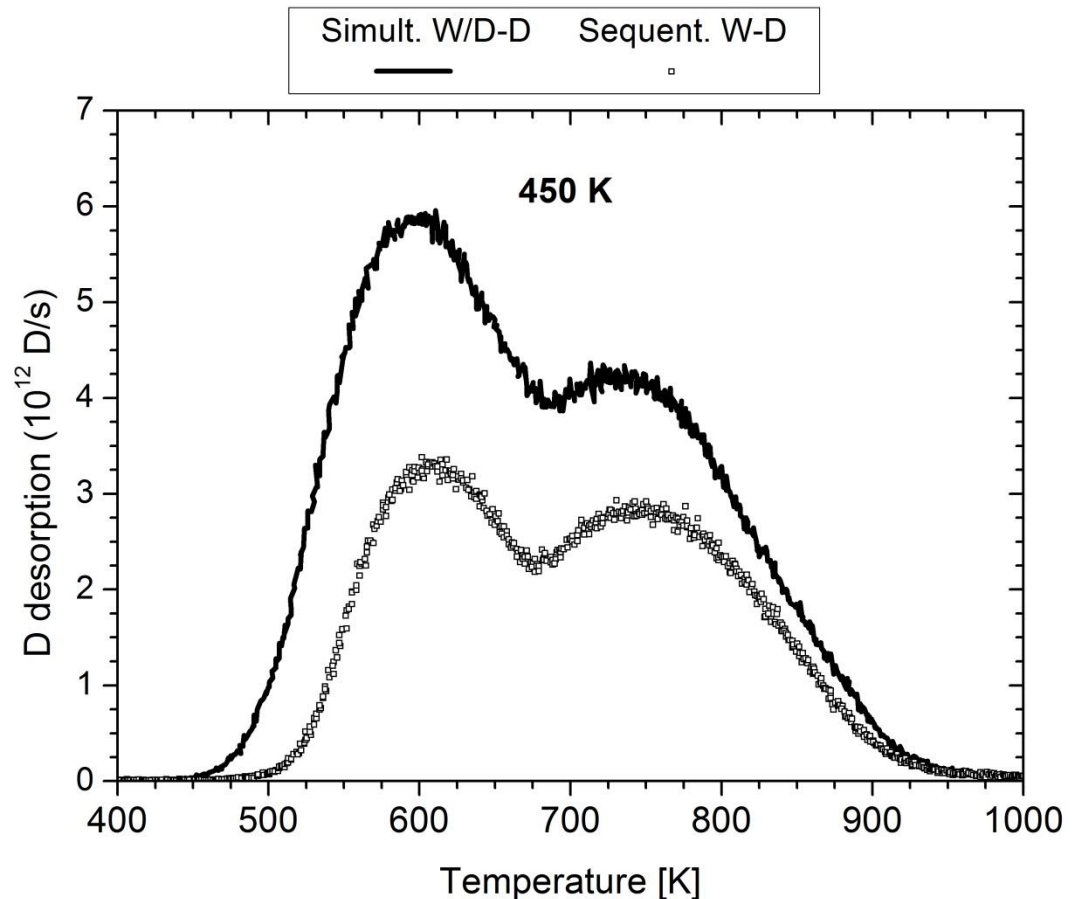
- Difference in D concentration in the region where D was trapped during the 1. step – simultaneous W/D
- Factor of 2 difference
- Comparison to older measurement – D depth profile similar with stepped distribution





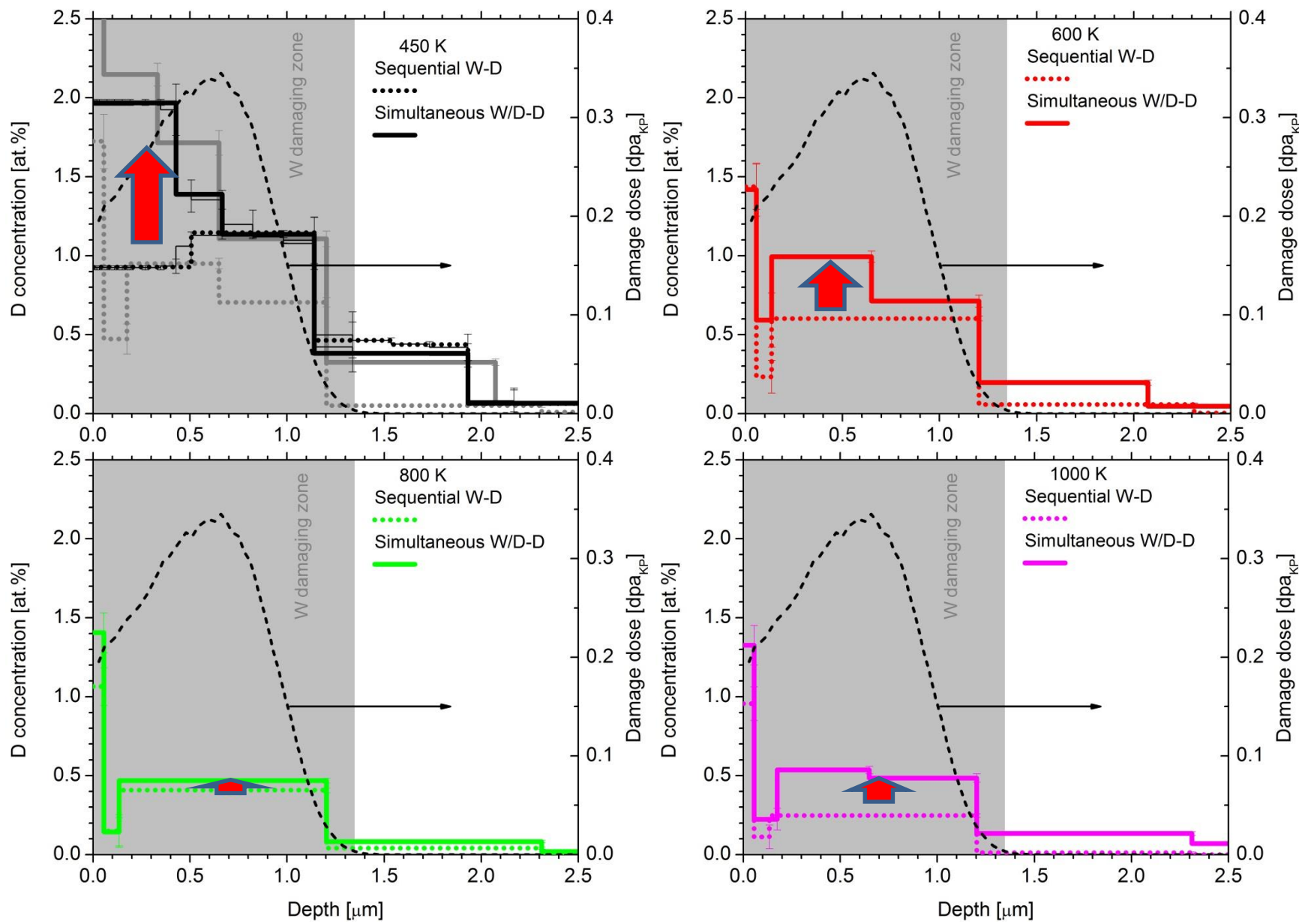
Comparison TDS sequential / simultaneous

- Defect population by 300eV/D ion exposure at 450K
- ✓ No drastic change in TDS peak shape - double peak for both cases
- ✓ Temperature dependence also for individual traps





D depth profile comparison – all temperatures

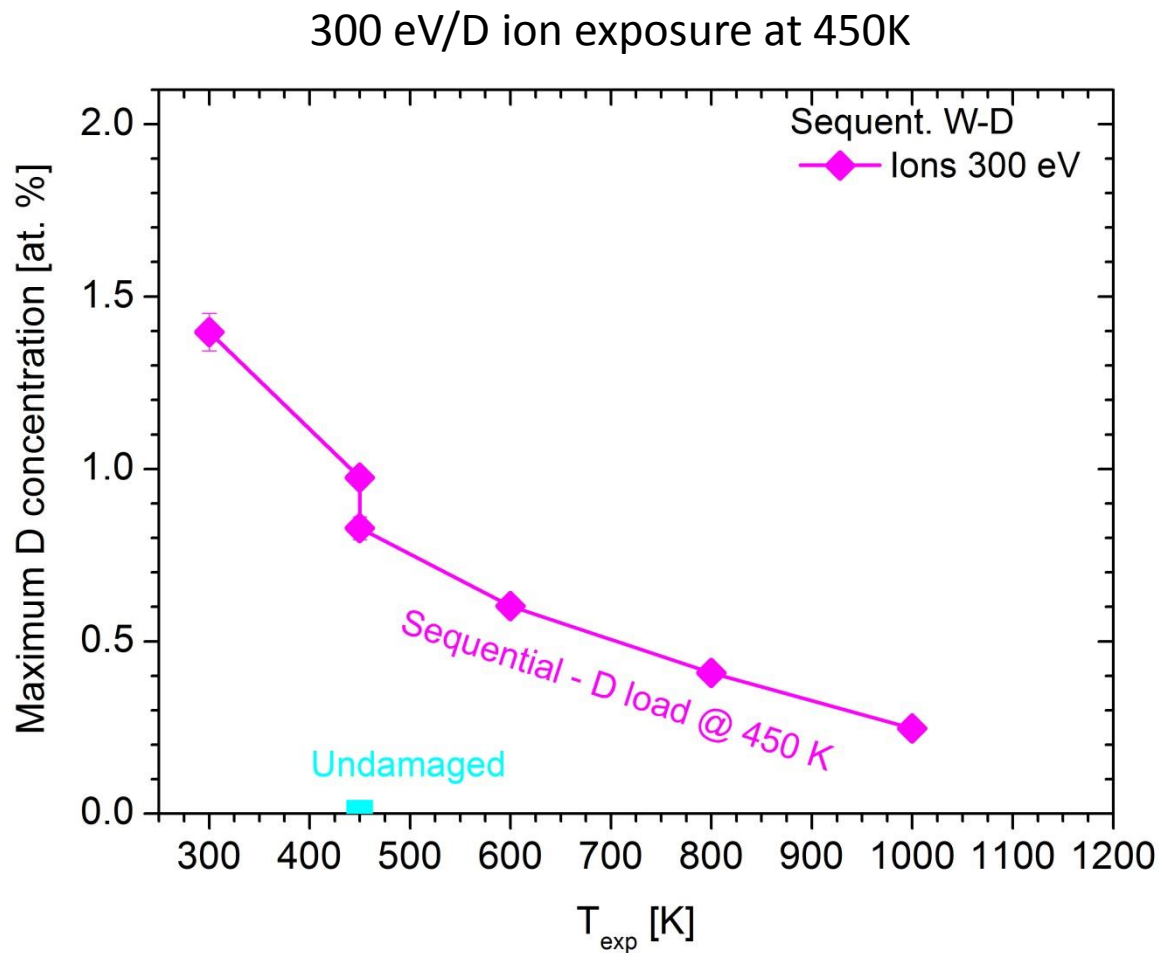




Sequential W-D exposure

➤ Sequential W-D exposure

- ✓ D concentration decreases with irradiation temperature
- ✓ Less defects created at elevated temperatures





Comparison to Simultaneous W/D-D exposure

➤ Sequential W-D exposure

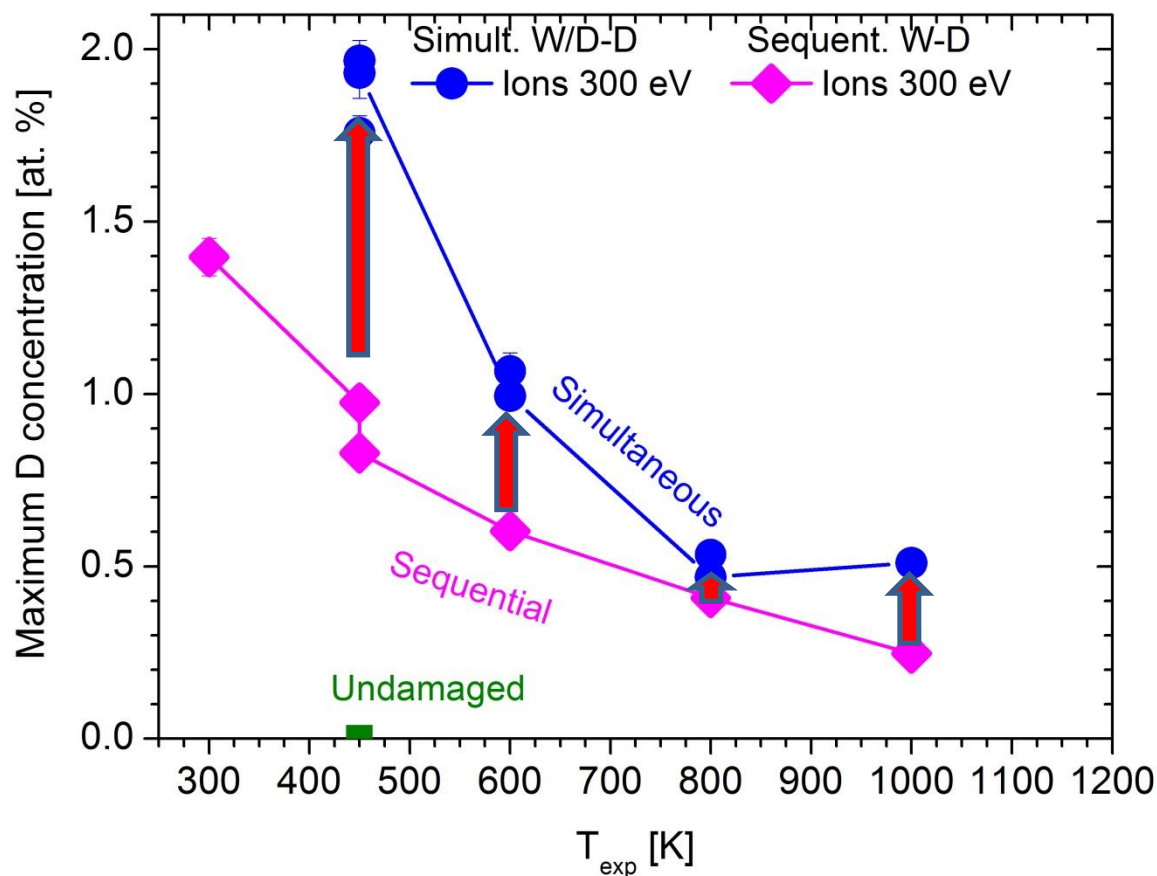
➤ Simultaneous W/D-D exposure

➤ Increase of D concentration – larger defect concentration

➤ Strong temperature dependence:

- 450 K – 2.1
- 600 K – 1.7
- 800 K – 1.1
- 1000 K – 2.1

300 eV/D ion exposure at 450K

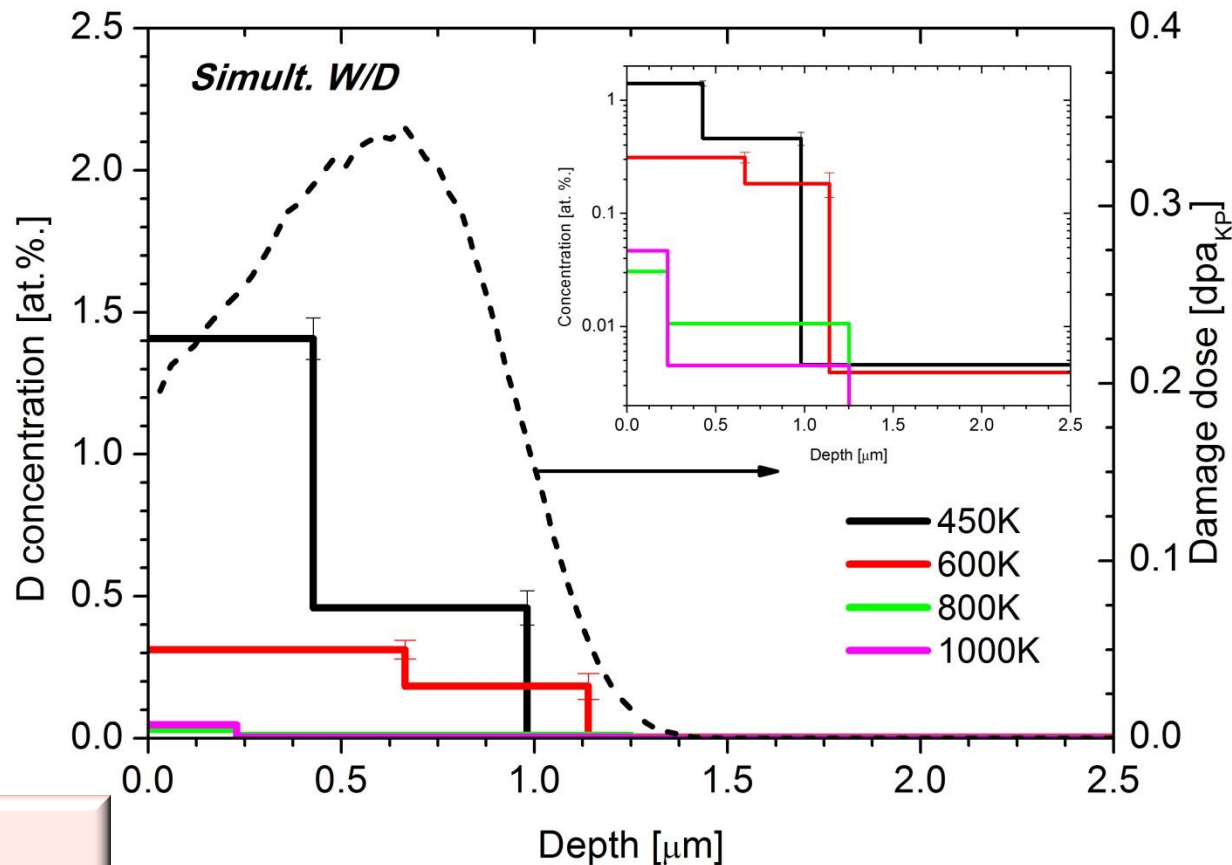


Simultaneous W/D exposure D depth profiles – all temperatures

Simultaneous W/D exposure:

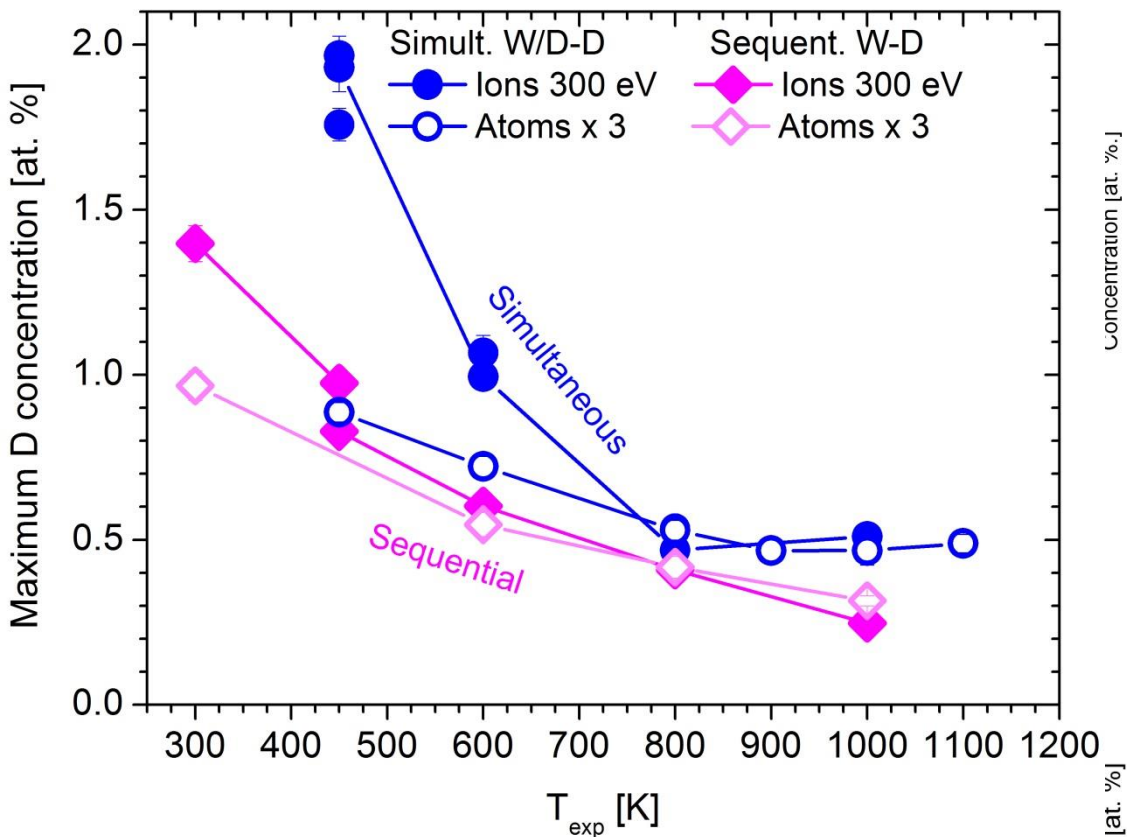
- ✓ Depth profiles after first 4h
- **Temperature determines the speed of diffusion and population of traps by D**
- **Lower D retention at high temperatures due to thermal D de-trapping**

Defect stabilization dependent on the D concentration during the simultaneous W/D

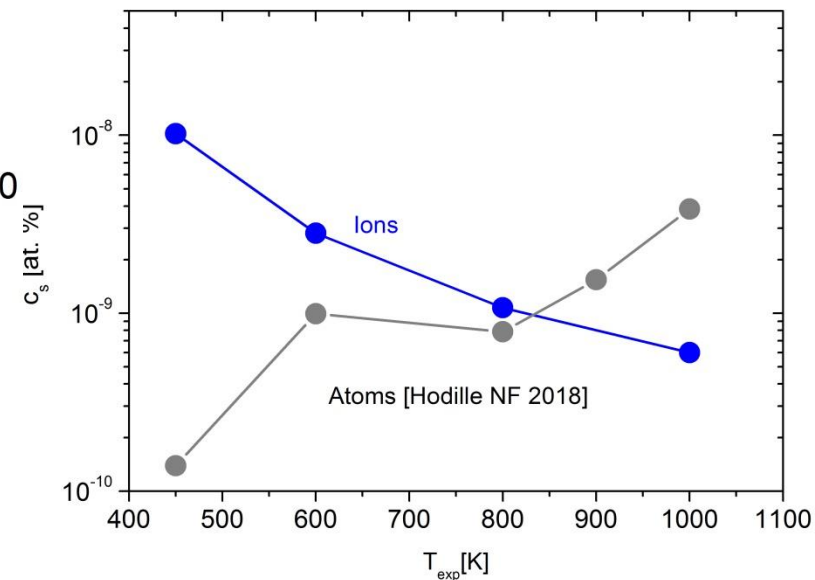
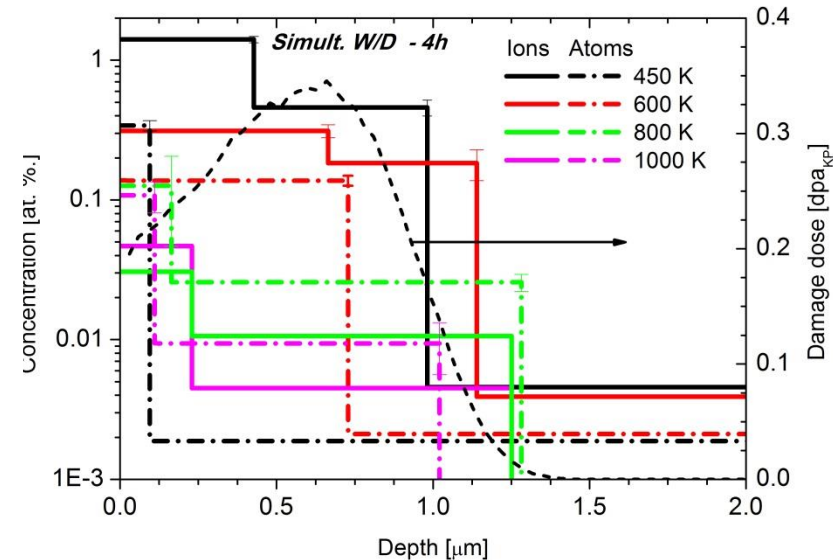




Comparison ions versus atoms



- D concentration during W/D exposure determines the efficiency of defect stabilization by D presence





Effect of presence of D Ab-initio calculations

Fusion device scenario neutron irradiation during D/T plasma exposure

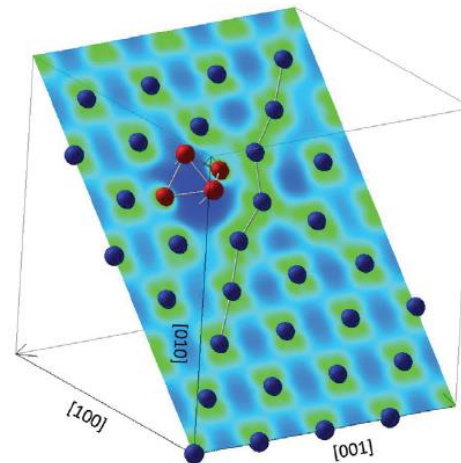
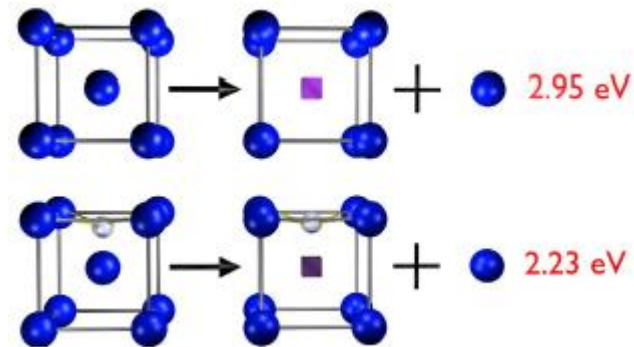
Two possible effects

Density Functional Theory (DFT) calculation with hydrogen in interstitial tetrahedral site in W [S.C. Middleburgh et al. , JNM 448 (2014) 270–275]:

- **25% lower than the vacancy formation energy in W without H.**
- **Higher probability of defect creation due to presence of H**

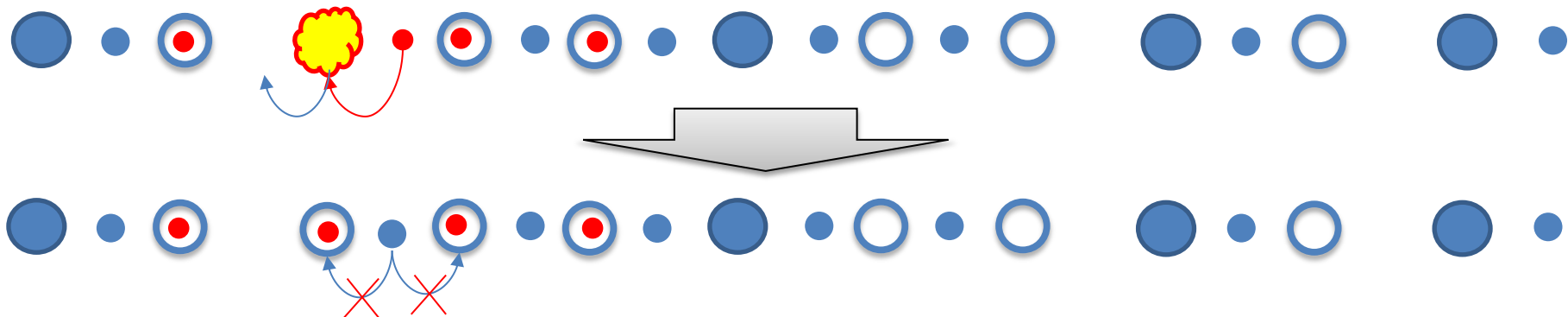
DFT calculation with hydrogen cluster in a vacancy in W [D. Kato et al. , NF 55 (2015) 083019]:

- Hydrogen cluster prevents vacancy from recombining with adjacent self-interstitial atoms (1 1 1-crowdion)
- **Lower probability for defect annihilation due to trapped D**





Stabilization by D trapping



We have upgraded the damage creation model, first introduced by Duesing *et al.* 1969, Ogorodnikov JAP 2008, Hodille NF 2018 - by including a stabilization mechanism:

$$\frac{dn_i(x, t)}{dt} = \frac{\Gamma \eta_i \theta(x)}{\rho} \left[1 - \frac{n_i(x, t)}{n_{i, \max}} \left(1 - \alpha_i \frac{n_i(x, t) - n_i^0(x, t)}{n_i(x, t)} \right) \right]$$

Defects are stabilized to a degree by D trapped in them, meaning that the probability for a Frenkel pair annihilation is lower. Stabilization is parametrized by a free parameter denoted as α_i .

Γ ... W ion flux ($\text{W m}^{-2}\text{s}^{-1}$)

η ... Creation probability (m^{-1})

$\theta(x)$... SRIM dam. distribution (1)

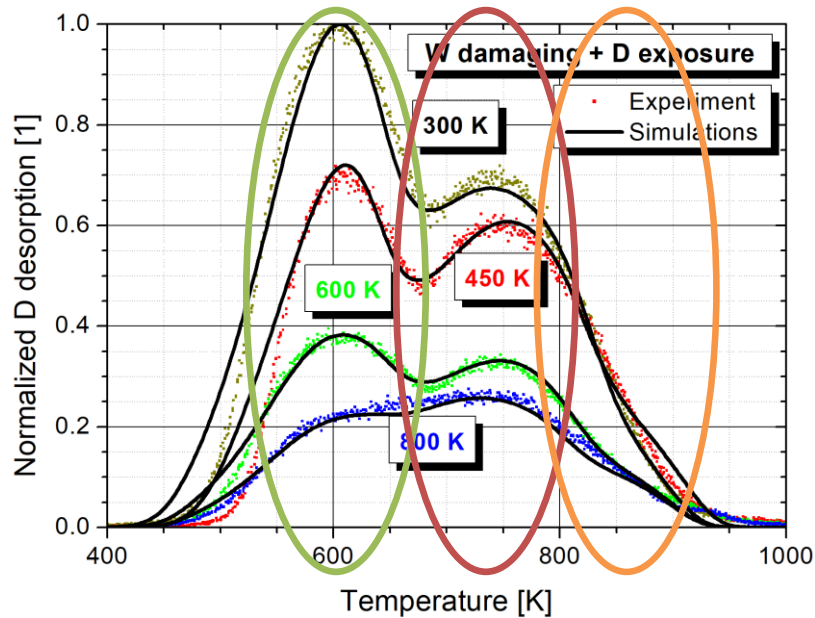
$n_{i, \max}$... Saturation density (1 (at. fr.))

M. Pečovnik et al. under review in Nucl. Fusion



Experiment versus modelling

TDS

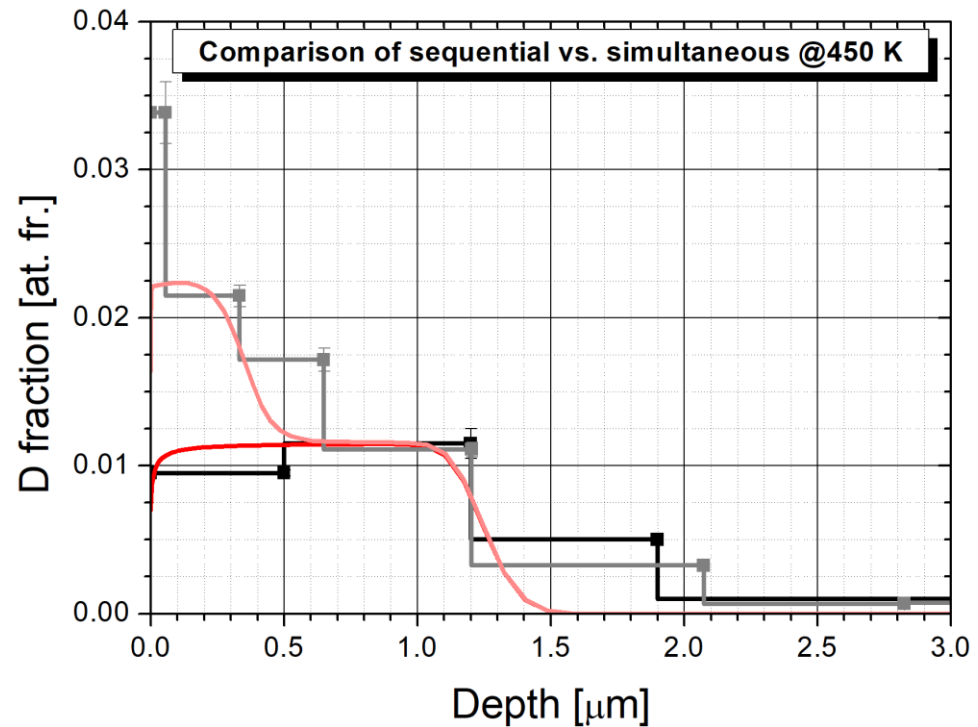


VACANCIES – 2 fill levels

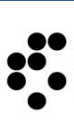
S. VACANCY CLUSTERS – 2 fill levels

L. VACANCY CLUSTERS – 1 fill level

D depth profiles



Stabilization by trapped D



Study of D presence on displacement damage stabilization

Sequential W-D experiment

- Decreased D retention with higher temperature

Simultaneous W/D-D experiment

- Effect of stabilization of defects increased for ion exposure as compared to atoms
- Observed temperature dependence of defect stabilization
- Concentration of created traps dependent on D concentration during the simultaneous W/D
- Increase of D concentration at 1000 K unclear
- Fusion scenario: higher fluxes of hydrogen fuel – higher D concentration at high temperatures – larger effect

References - ions

- S. Markelj, et al, Nucl. Fusion (2019) in press
- M. Pečovnik et al. under review Nucl. Fusion

References atoms:

- S. Markelj, et al, Nuclear Materials and Energy 12 (2017) 169.
- E. Hodille et al. Nucl. Fusion **59** (2019) 016011



D mobile concentration comparison

